

LOR 3A Photoresist Process

- Clean a sample with acetone and IPA.
- Bake sample on hotplate @ 110°C for 5min for dehydration
- Spin coat LOR 3A on the wafer using the settings with spin speed of 3000 rpm for spin time of 35 sec
- Bake sample hot plate @ 180°C for 5 min
- Spin cot Shipley 1805 on the sample using the settings with spin speed of 4000 rpm for spin time of 40 sec
- Bake sample on hot plate @ 110°C for 90 sec
- Expose sample 100 mJ/cm².
- Develop sample with MIF 319 for 45-60 sec or CD 26 for 60-90 sec and rinse with DI water for 30 sec.
- Check for the undercut profile.
- When you use LOR Photoresists, after lift-off with acetone, dip sample into developer for 1 minute. LOR does not dissolve well in acetone.